

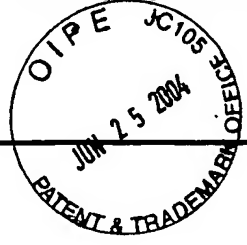
LFW

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))	Docket No. 112857-476
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In Re Application Of: **Goshi Biwa et al.**

Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/786,667	February 25, 2004	Unknown	29175	2812	2982

Title: **METHOD OF FABRICATING SEMICONDUCTOR DEVICE AND SEMICONDUCTOR DEVICE**



Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- ☐ the statement specified in 37 CFR 1.97(e);
- OR**
- ☐ the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
112857-476

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10/786,667	February 25, 2004	Unknown	29175	2812	2982

METHOD OF FABRICATING SEMICONDUCTOR DEVICE AND SEMICONDUCTOR DEVICE



Payment of Fee


(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **02-1818** as described below.
- ☐ Charge the amount of _____
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.

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 Signature of Person Mailing Correspondence
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***This certificate may only be used if paying by deposit account.**



Signature

Dated: **June 22, 2004**

Thomas C. Basso
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Goshi Biwa et al.
Appl. No.: 10/786,667
Filed: February 25, 2004
Title: METHOD OF FABRICATING SEMICONDUCTOR DEVICE AND
SEMICONDUCTOR DEVICE
Art Unit: 2812
Examiner: Unknown
Docket No.: 112857-476

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 37 C.F.R. 1.97, and 37 C.F.R. 1.98, Applicants request that a citation and examination of the references cited below, and on the attached PTO-1449 form, copies of which are enclosed, be made during the course of examination of the above-identified application for United States patent.

FOREIGN PATENT DOCUMENTS

<u>Document No.</u>	<u>Date</u>	<u>Country</u>
WO 98/14986	April 9, 1998	PCT
10-125929	May 15, 1998	Japan
2000-332343	November 30, 2000	Japan
2001-501778	June 2, 2001	Japan

OTHER DOCUMENTS

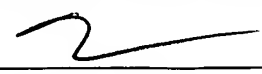
Kapolnek et al., "Spatial control of InGaN luminescence by MOCVD selective epitaxy", Journal of Crystal Growth, 189/190 (1998) pages 83-86.

Applicants look forward to early and favorable consideration of this matter.

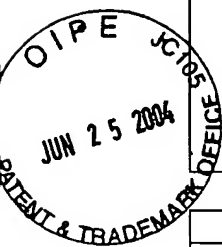
Respectfully submitted,

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BY


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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 112857-476	Application No. 10/786,667
	Applicant Biwa et al	
	Filing Date 02/25/04	Group 2812

U.S. PATENT DOCUMENTS							
Examiner's Initials		Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS								
Examiner's Initials		Document Number	Publication Date	Country	Class	Subclass	Translation	
							Yes	No
		WO 98/14986	04-09-98	PCT				
		10-125929	05-15-98	Japan				
		2000-332343	11-30-00	Japan				
		2001-501778	06-02-01	Japan				

Examiner's Initials		OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
		Kapolnek et al, "Spatial control of InGaN luminescence by MOCVD selective epitaxy", Journal of Crystal Growth 189/190 (1998) pages 83-86.

Examiner:	Date Considered:
*Examiner: Initial if citation considered, whether or not citation is in conformance with PEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	